

Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

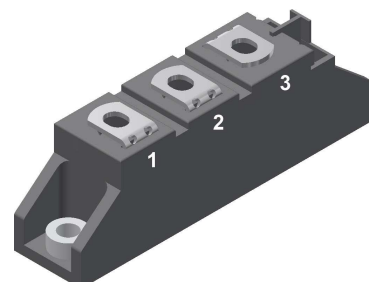
$$I_{FAV} = 110 \text{ A}$$

$$V_F = 1.14 \text{ V}$$

Phase leg

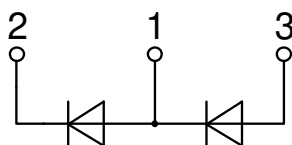
Part number

MDMA110P1200TG



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

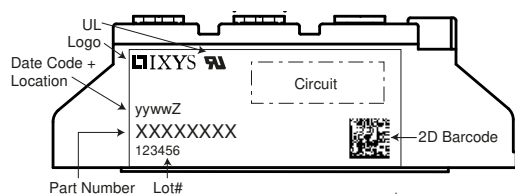
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 110\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.21	V
		$I_F = 220\text{ A}$				1.44	V
		$I_F = 110\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.14	V
		$I_F = 220\text{ A}$				1.44	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ d = 0.5			110	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.82	V
r_F	slope resistance					2.8	m Ω
R_{thJC}	thermal resistance junction to case					0.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				415	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			2.00	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			2.16	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			1.70	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.84	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			20.0	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			19.4	kA ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			14.5	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			14.0	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			73		pF

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					76		g
M_D	mounting torque			2.5		4	Nm
M_T	terminal torque			2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800 4000			V V



Part description

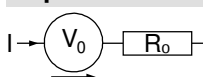
M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 110 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA110P1200TG	MDMA110P1200TG	Box	36	514304

Equivalent Circuits for Simulation

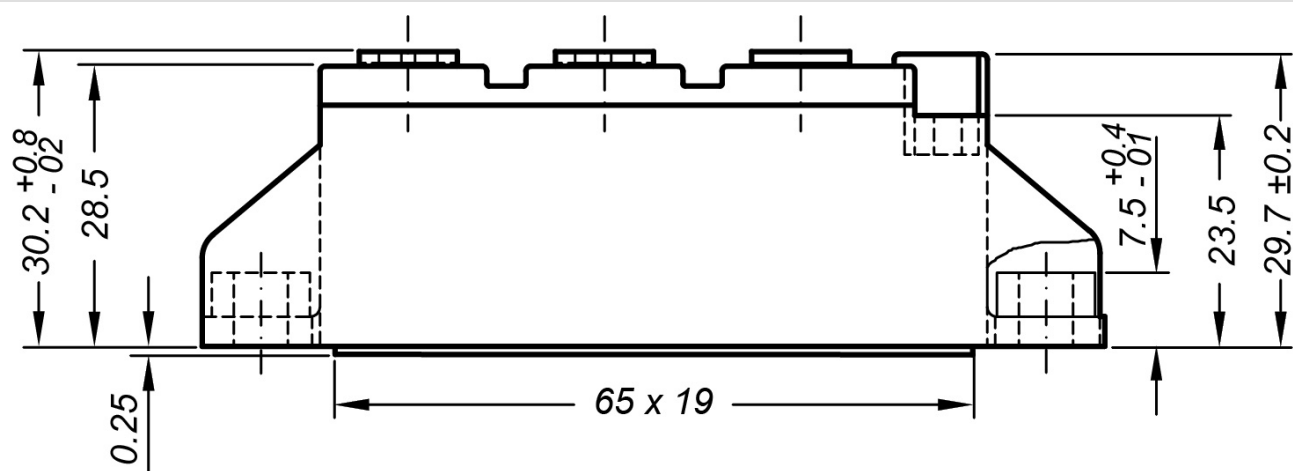
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

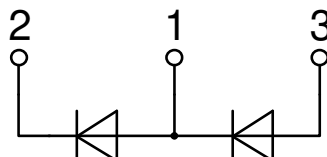
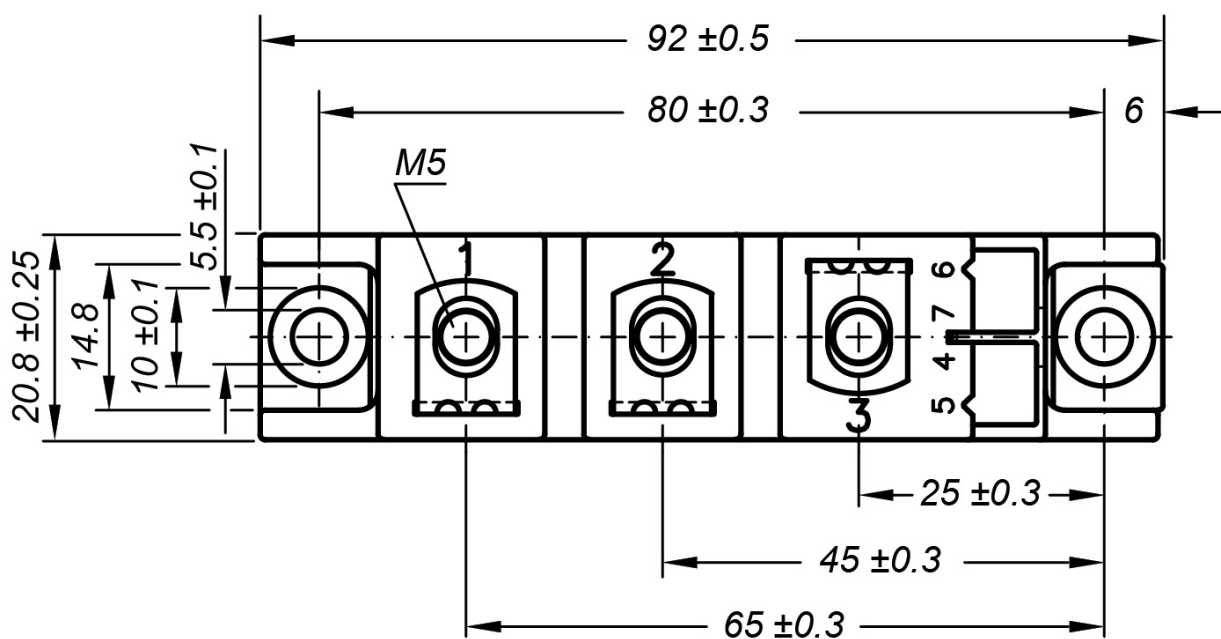


Rectifier

$V_{0\max}$	threshold voltage	0.82	V
$R_{0\max}$	slope resistance *	1.6	mΩ



General tolerance: DIN ISO 2768 class „c“



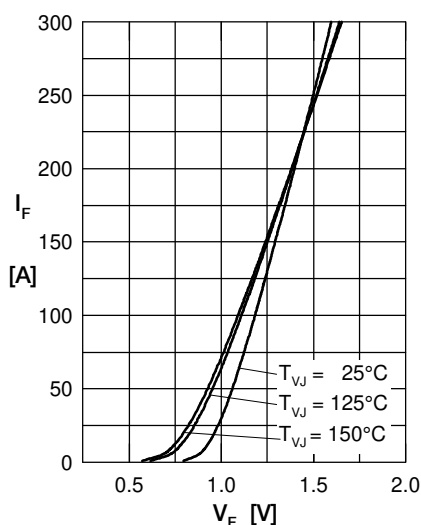
Rectifier


Fig. 1 Forward current versus voltage drop per diode

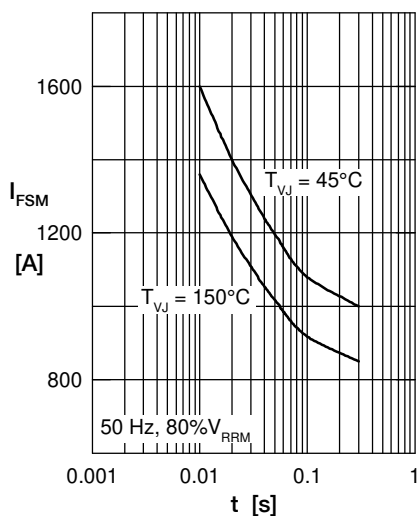


Fig. 2 Surge overload current vs. time per diode

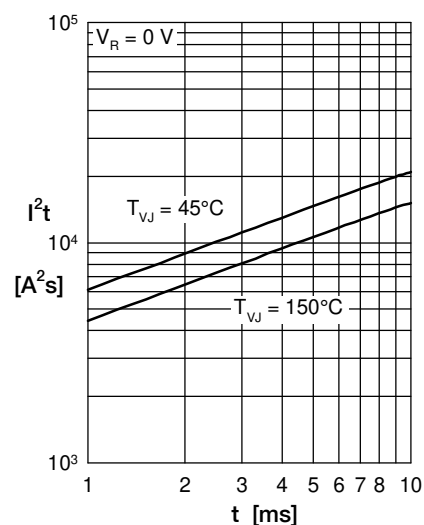
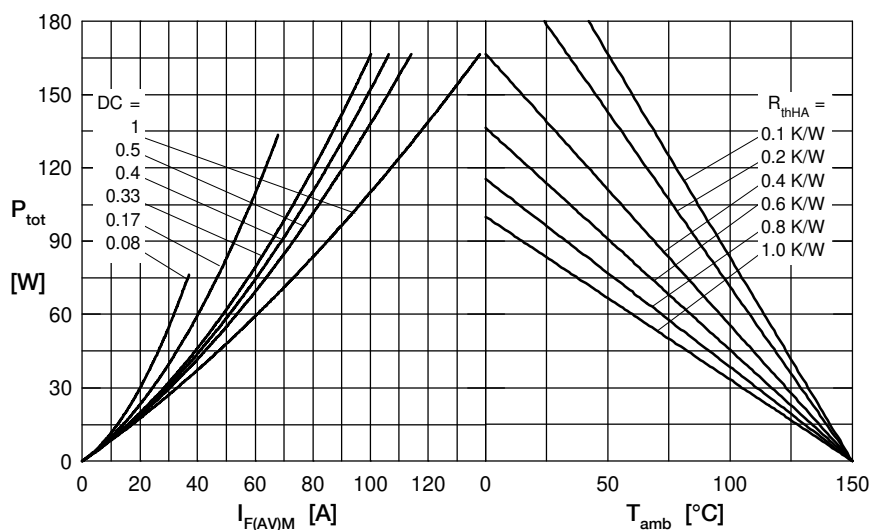

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

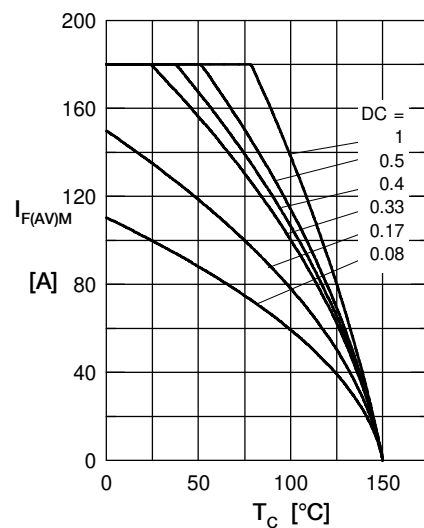


Fig. 5 Max. forward current vs. case temperature per diode

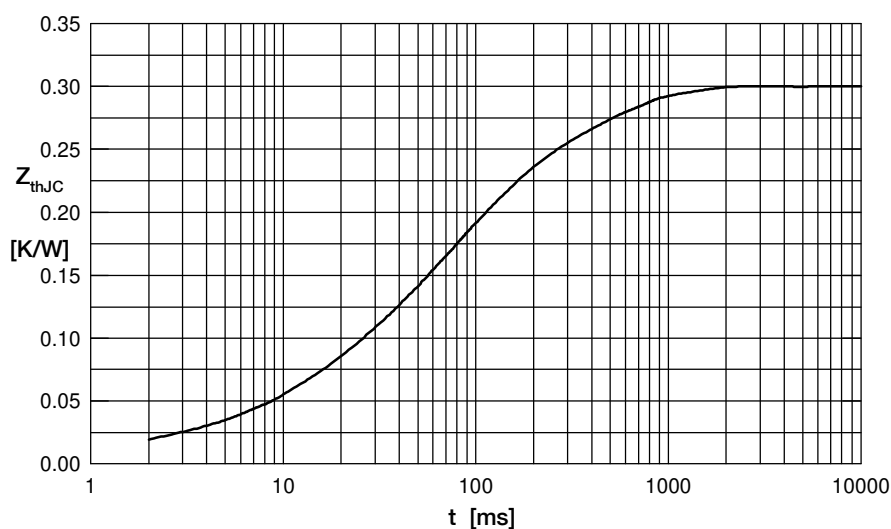


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.01	0.001
2	0.04	0.013
3	0.16	0.070
4	0.09	0.400